



# BTW67 and BTW69 Series

STANDARD

50A SCRs

## MAIN FEATURES:

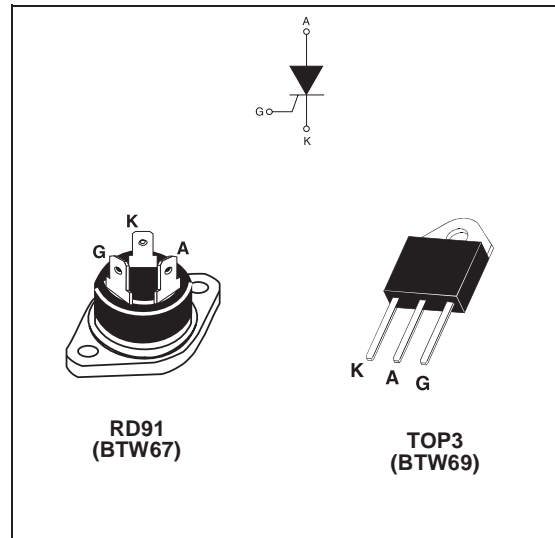
Symbol	Value	Unit
$I_{T(RMS)}$	50	A
$V_{DRM}/V_{RRM}$	600 to 1200	V
$I_{GT}$	80	mA

## DESCRIPTION

Available in high power packages, the BTW67 / BTW69 Series is suitable in applications where power handling and power dissipation are critical, such as solid state relays, welding equipment, high power motor control.

Based on a clip assembly technology, they offer a superior performance in surge current handling capabilities.

Thanks to their internal ceramic pad, they provide high voltage insulation (2500V RMS), complying with UL standards (file ref: E81734).



## ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	RD91 T <sub>c</sub> = 70°C	50 A
		TOP3 Ins. T <sub>c</sub> = 75°C	
$I_{T(AV)}$	Average on-state current (180° conduction angle)	RD91 T <sub>c</sub> = 70°C	32 A
		TOP3 Ins. T <sub>c</sub> = 75°C	
$I_{TSM}$	Non repetitive surge peak on-state current	tp = 8.3 ms T <sub>j</sub> = 25°C	610 A
		tp = 10 ms	
$I^2t$	$I^2t$ Value for fusing	T <sub>j</sub> = 25°C	1680 A <sup>2</sup> s
di/dt	Critical rate of rise of on-state current I <sub>G</sub> = 2 x I <sub>GT</sub> , tr ≤ 100 ns	F = 60 Hz T <sub>j</sub> = 125°C	50 A/μs
I <sub>GM</sub>	Peak gate current	tp = 20 μs T <sub>j</sub> = 125°C	8 A
P <sub>G(AV)</sub>	Average gate power dissipation	T <sub>j</sub> = 125°C	1 W
T <sub>stg</sub> T <sub>j</sub>	Storage junction temperature range Operating junction temperature range		- 40 to + 150 - 40 to + 125 °C
V <sub>RGM</sub>	Maximum peak reverse gate voltage		5 V

## BTW67 and BTW69 Series

### ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25°C, unless otherwise specified)

Symbol	Test Conditions		Value	Unit	
I <sub>GT</sub>	V <sub>D</sub> = 12 V    R <sub>L</sub> = 33 Ω	MIN.	8	mA	
		MAX.	80		
V <sub>GT</sub>		MAX.	1.3	V	
V <sub>GD</sub>	V <sub>D</sub> = V <sub>DRM</sub> R <sub>L</sub> = 3.3 kΩ	T <sub>j</sub> = 125°C	MIN.	0.2	V
I <sub>H</sub>	I <sub>T</sub> = 500 mA    Gate open		MAX.	150	mA
I <sub>L</sub>	I <sub>G</sub> = 1.2 I <sub>GT</sub>		MAX.	200	mA
dV/dt	V <sub>D</sub> = 67 % V <sub>DRM</sub> Gate open	T <sub>j</sub> = 125°C	MIN.	1000	V/μs
V <sub>TM</sub>	I <sub>TM</sub> = 100 A    t <sub>p</sub> = 380 μs	T <sub>j</sub> = 25°C	MAX.	1.9	V
V <sub>t0</sub>	Threshold voltage	T <sub>j</sub> = 125°C	MAX.	1.0	V
R <sub>d</sub>	Dynamic resistance	T <sub>j</sub> = 125°C	MAX.	8.5	mΩ
I <sub>DRM</sub> I <sub>RRM</sub>	V <sub>DRM</sub> = V <sub>RRM</sub>	T <sub>j</sub> = 25°C	MAX.	10	μA
		T <sub>j</sub> = 125°C		5	mA

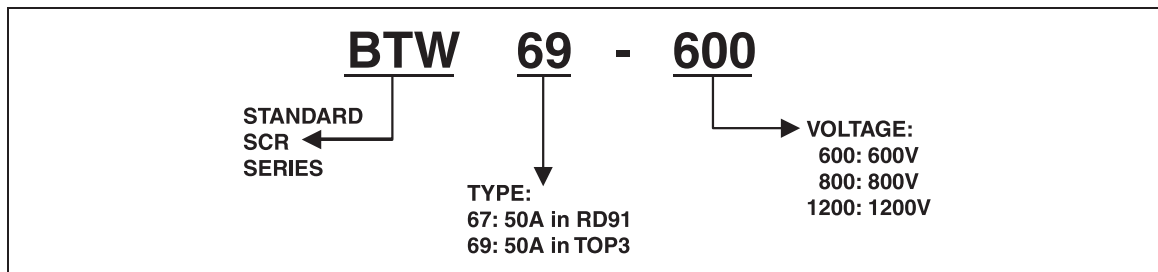
### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
R <sub>th(j-c)</sub>	Junction to case (DC)	RD91 (Insulated)	1.0	°C/W
		TOP3 Insulated	0.9	
R <sub>th(j-a)</sub>	Junction to ambient	TOP3 Insulated	50	°C/W

### PRODUCT SELECTOR

Part Number	Voltage (xxx)			Sensitivity	Package
	600 V	800 V	1200 V		
BTW67-xxx	X	X	X	80 mA	RD91
BTW69-xxx	X	X	X	80 mA	TOP3 Ins.

### ORDERING INFORMATION

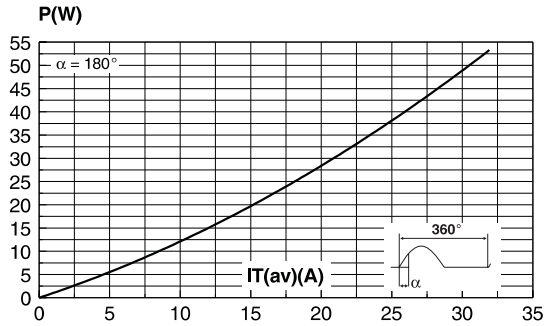


### OTHER INFORMATION

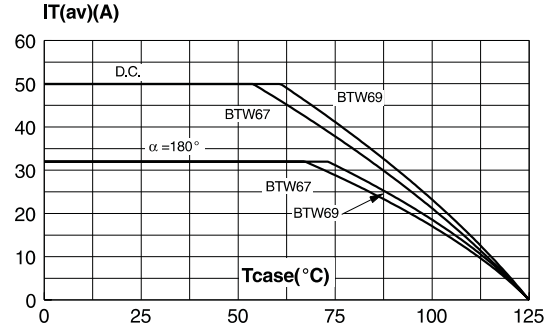
Part Number	Marking	Weight	Base Quantity	Packing mode
BTW67-xxx	BTW67xxx	20.0 g	25	Bulk
BTW69-xxx	BTW69xxx	4.5 g	120	Bulk

Note: xxx = voltage

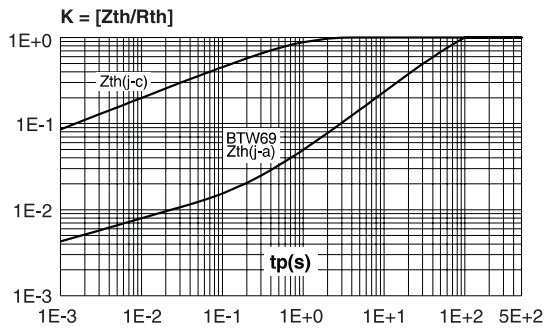
**Fig. 1:** Maximum average power dissipation versus average on-state current.



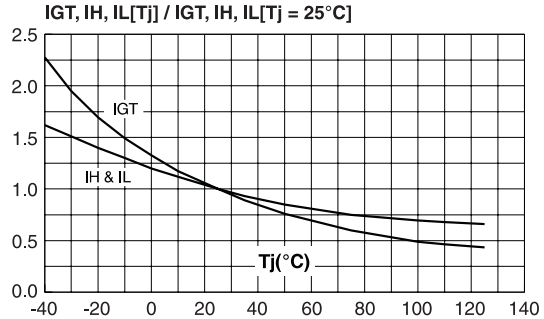
**Fig. 2:** Average and D.C. on-state current versus case temperature.



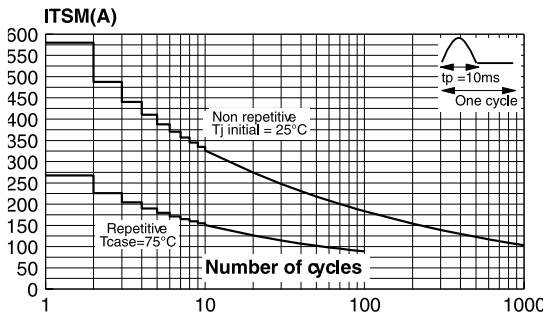
**Fig. 3:** Relative variation of thermal impedance versus pulse duration.



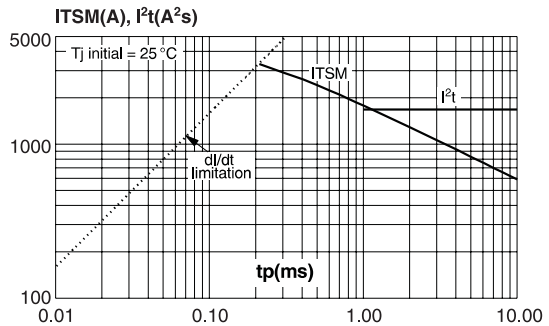
**Fig. 4:** Relative variation of gate trigger current, holding current and latching current versus junction temperature.



**Fig. 5:** Surge peak on-state current versus number of cycles.

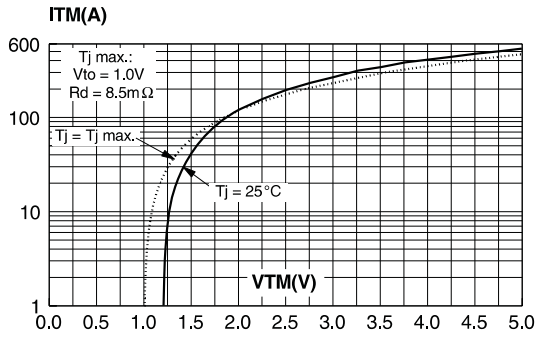


**Fig. 6:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $tp < 10ms$ , and corresponding value of  $I^2t$ .



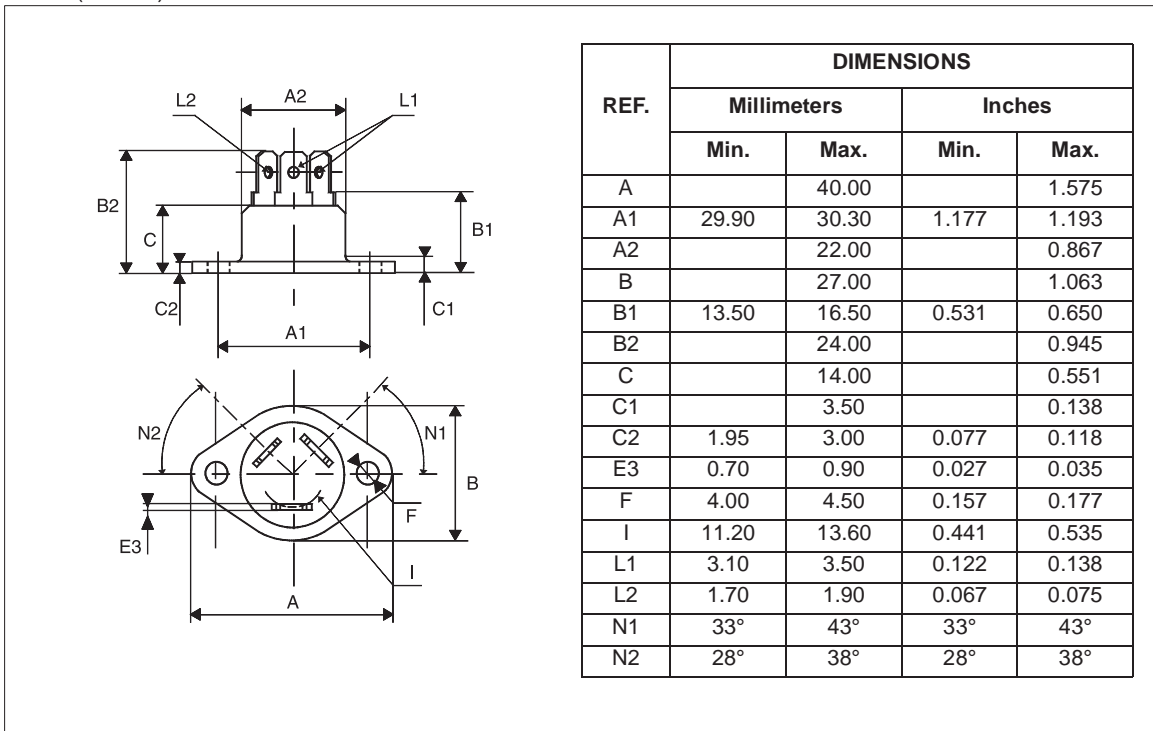
## BTW67 and BTW69 Series

**Fig. 7:** On-state characteristics (maximum values).



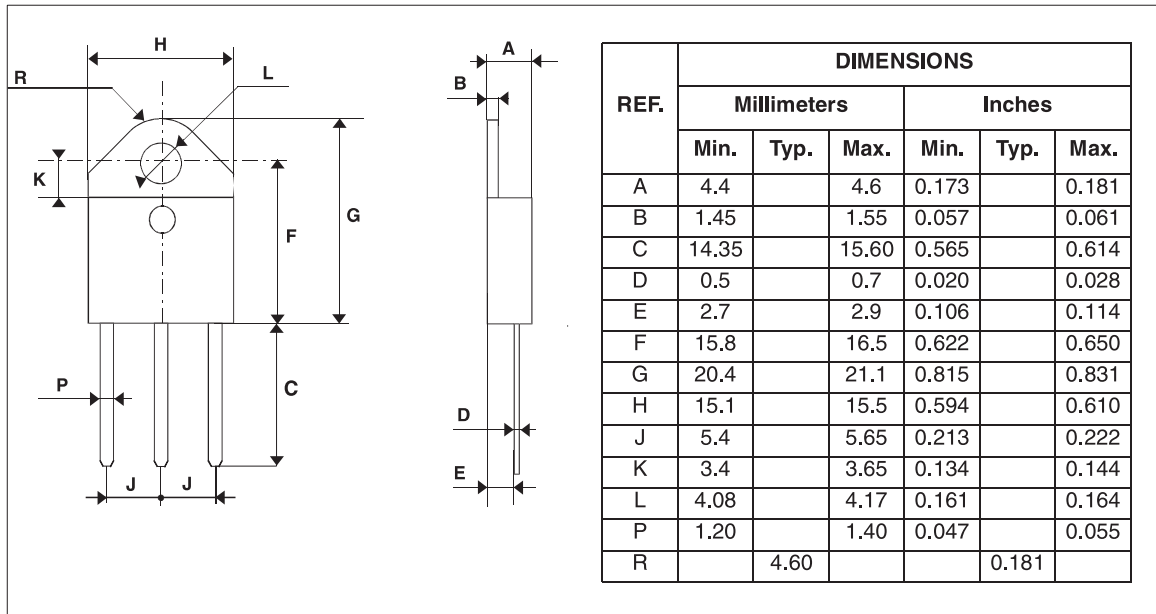
### PACKAGE MECHANICAL DATA

RD91 (Plastic)



**PACKAGE MECHANICAL DATA**

TOP3 Ins.(Plastic)



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